# PROCESS CPD96V

## Schottky Diode

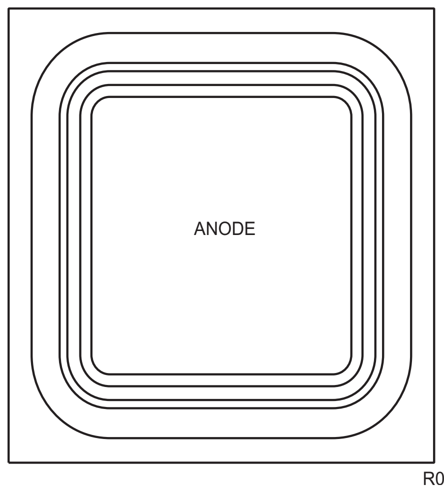
### 500mA Low $V_F$ Schottky Diode Chip

**Central™ Semiconductor Corp.**

## PROCESS DETAILS

| Process | EPITAXIAL PLANAR |
|---|---|
| Die Size | 20 x 20 MILS |
| Die Thickness | 7.1 MILS |
| Anode Bonding Pad Area | 16 x 16 MILS |
| Top Side Metalization | Al - 20,000Å |
| Back Side Metalization | Au - 12,000Å |

## GEOMETRY




BACKSIDE CATHODE

**GROSS DIE PER 4 INCH WAFER**

28,028

**PRINCIPAL DEVICE TYPES**

CMLSH05-4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Hauppauge, NY 11788 USA
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R3 (15-March 2006)

# Central Semiconductor Corp.

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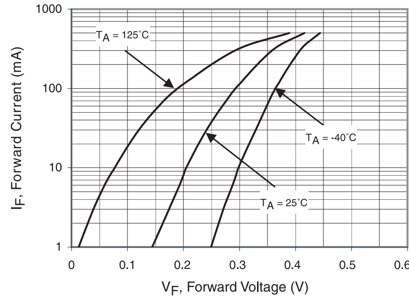
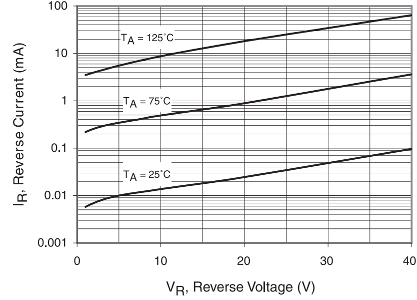
## Typical Electrical Characteristics

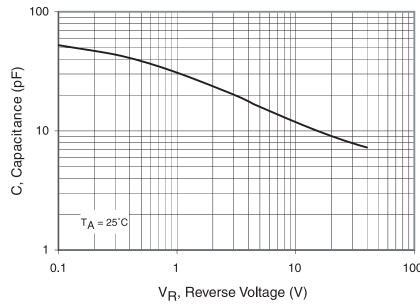
Forward Voltage



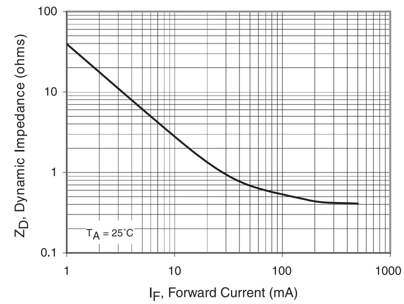

Leakage Current



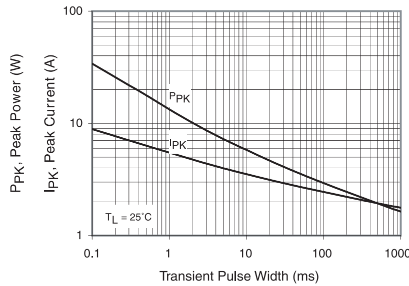

Capacitance



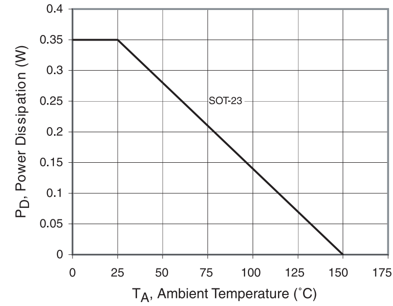

Forward Dynamic Impedance




Transient Peak Power and Peak Current Capacity




Power Derating





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